METHOD FOR ETCHING ETCHING TARGET LAYER

ABSTRACT

Disclosed is an etching method for etching an etching target layer. The etching method includes: a first step of depositing a plasma reaction product on a mask layer made of an organic film formed on the etching target layer; and after the first step, a second step of etching the etching target layer. The mask layer includes a coarse region in which a plurality of openings are formed, and a dense region surrounding the coarse region. The mask layer exists more densely in the dense region than in the coarse region. The coarse region includes a first region and a second region positioned close to the dense region compared to the first region. In the second step of the etching method, a width of the openings in the first region becomes narrower than a width of the openings in the second region.

(Fig. 1)